

GSDSS1□□A1F Series

Schottky Barrier Diode

Product Description

Reverse Voltage 40V to 100V.
Forward Current 1.0A



Features

- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- RoHS Compliant and Halogen Free

Mechanical Data

- Case : Molded Plastic, SMAF Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Polarity: Color Band denotes Cathode End

Package and Pin Assignment

SMAF		Equivalent Circuit
		
Pin	Description	
1	Anode	
2	Cathode	

Ordering and Marking Information

Ordering Information			
Part Number	Package	Marking Code	Quantity/Reel
GSDSS14A1F	SMAF	SS14F	3000 PCS
GSDSS16A1F	SMAF	SS16F	3000 PCS
GSDSS110A1F	SMAF	SS110F	3000 PCS

GSDSS1 □ □ A1 F		
- Product Code: GSDSS1	- Voltage Code: □ □ is 4, 6, and 10. For examples 4 stands for 40V and 10 stands for 100V	- Package Code: A1 for SMAF Package
- Green Level: F for RoHS Compliant and Halogen Free		

Marking Information

SS1 \square \square F

- **Product Code:**

SS1

- **Voltage Code:**

\square \square is 4, 6, and 10.

For examples 4 stands for 40V
and 10 stands for 100V

- **Green Level:**

F for RoHS Compliant and
Halogen Free

Electrical Characteristics

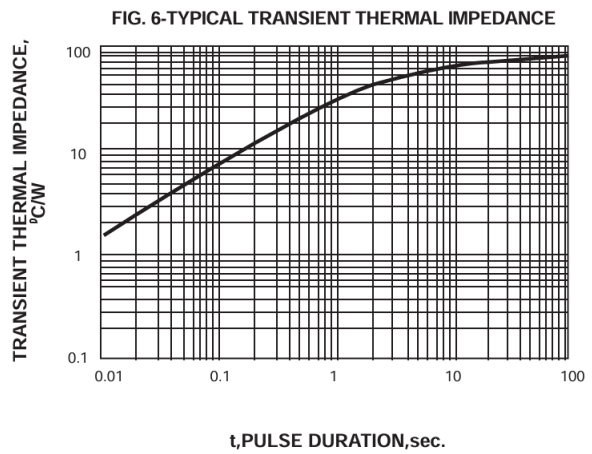
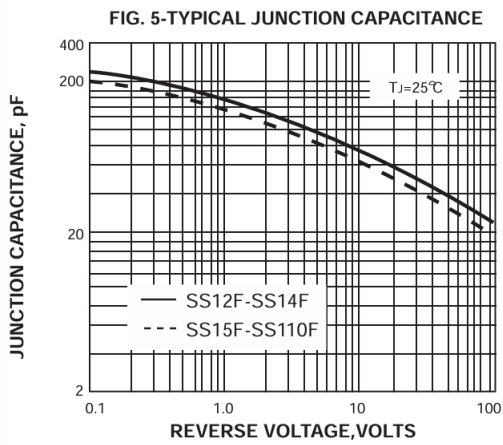
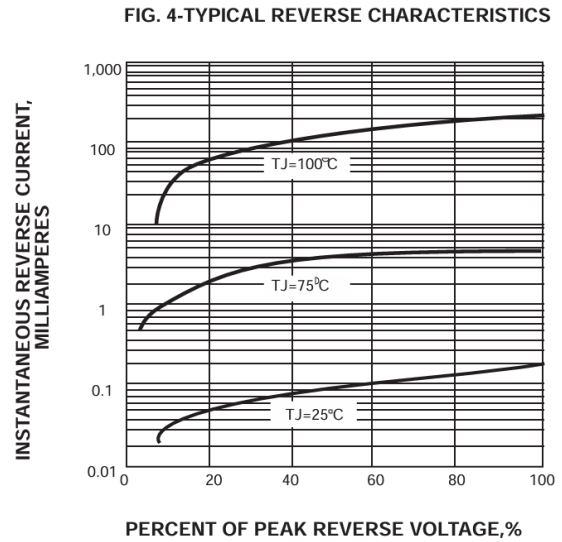
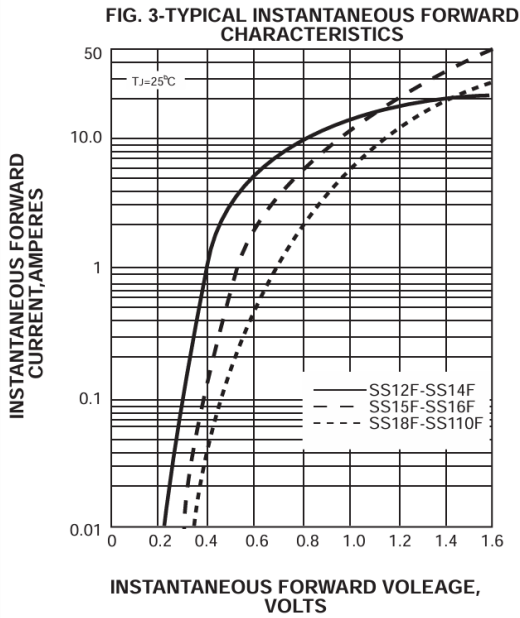
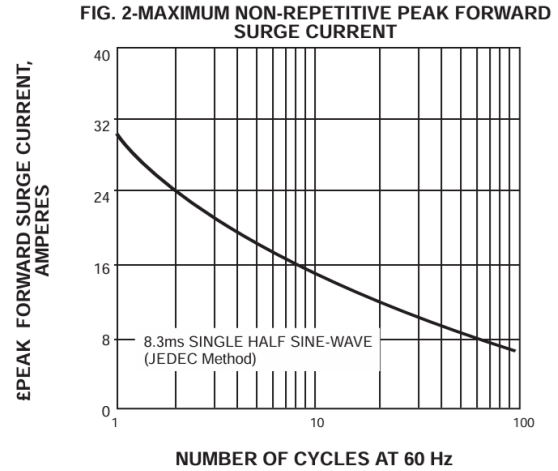
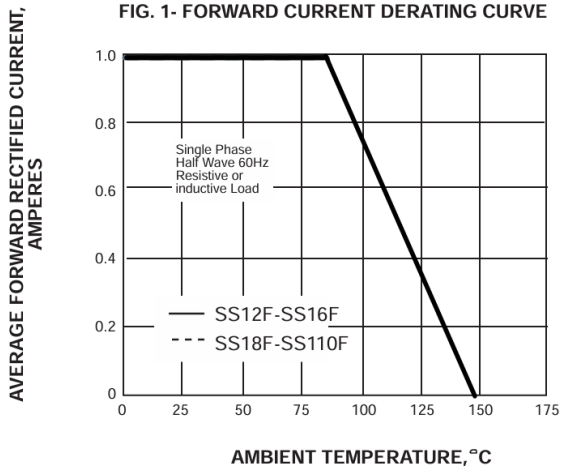
(Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60HZ, resistive or inductive load. For capacitive load, derate current by 20%.)

Symbol	Description	14A1F	16A1F	110A1F	Unit
V _{RRM}	Maximum Repetitive Peak Reverse Voltage	40	60	100	V
V _{RMS}	Maximum RMS Voltage	28	42	70	V
V _{DC}	Maximum DC Blocking Voltage	40	60	100	V
I _(AV)	Maximum Average Forward Rectified Current	1.0			A
I _{FSM}	Peak Forward Surge Current, 8.3ms Single Half-Sine-Wave Superimposed on rated Load (JEDEC Method)	30			A
V _F	Maximum Forward Voltage at 1.0A	0.55	0.70	0.85	V
I _R	Maximum Reverse Current at Rated DC Blocking Voltage T _A =25°C	0.5			mA
	T _A =100°C	6.0	5.0		mA
C _J	Typical Junction Capacitance ⁽¹⁾	110	90		pF
R _{θJA}	Typical Thermal Resistance ¹	88			°C/W
T _J	Junction Temperature Range	-65 to 150			°C
T _{STG}	Storage Temperature Range	-65 to 150			°C

NOTES:

1. Measured at 1MHz and applied reverse voltage of 4.0 V_{DC}.
2. Mounted with 0.2 x 0.2" (5.0 x 5.0mm) Copper Pad Areas

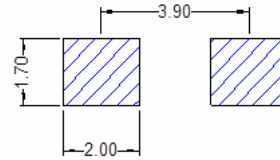
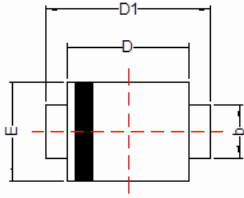
Typical Characteristics (Ratings at 25°C Ambient Temperature Unless Otherwise Specified.)



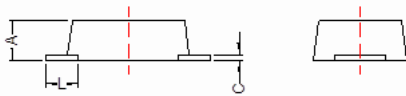
SMAF

Package Dimension

Recommended Land Pattern



(Unit: mm)



Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.90	1.30	0.035	0.051
b	1.20	1.60	0.047	0.063
D	3.25	3.75	0.128	0.147
D1	4.30	4.90	0.169	0.193
E	2.30	2.70	0.091	0.106
c	0.05	0.3	0.002	0.012
L	1.20 MAX		0.047 MAX	





NOTE:



Dimensions are exclusive of Burrs, Mold Flash and Tie Bar extrusions.

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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587